

*Q1 F1  
CMD.*  
and formed on the first region, the first and second regions having an identical conductivity type.

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*F2  
Q2*  
4. (Four Times Amended) A semiconductor device comprising:  
an insulated gate field effect transistor having a pair of main electrodes used as source and drain electrodes, a channel forming region provided between the pair of main electrodes, an insulating gate film formed on the channel forming region, and a gate electrode formed on the insulating gate film, and provided with a first region including at least a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including the first group IV element and formed on the first region, the first and second regions having an identical conductivity type; and  
a silicide electrode formed in contact with the second region of the gate electrode, and being substantially free from the second group IV element.

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*F3  
Q3*  
11. (Four Times Amended) A semiconductor device comprising:  
an insulated gate field effect transistor having a pair of main electrodes used as source and drain electrodes, a channel forming region provided between the pair of main electrodes, an insulating gate film formed on the channel forming region, and a gate electrode formed on the insulating gate film, and provided with a first region including at least a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including a multiple element compound including at least the first and second group IV elements and metal, and formed on the first region, the first and second regions having an identical conductivity type; and  
a silicide electrode formed in contact with the second region of the gate electrode, including the first group IV element and metal, and being substantially free from the second group IV element.

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*F4  
Q4*  
15. (Three Times Amended) A semiconductor device comprising:  
a semiconductor region of a first conductivity type;

an epitaxial growth layer formed on the semiconductor region and having a first region of the first conductivity type including at least a first group IV element and a second group IV element and formed in contact with the semiconductor region, and a second region of the first conductivity type including the first group IV element and formed in contact with the first region; and

a silicide electrode formed on the second region of the epitaxial growth layer.

23. (Four Times Amended) A semiconductor device comprising:

an insulated gate field effect transistor having a pair of main electrodes used as source and drain electrodes, a channel forming region provided between the pair of main electrodes, an insulating gate film formed on the channel forming region, and a gate electrode formed on the insulating gate film, and provided with a first region including at least a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including the first group IV element and formed on the first region, the first and second regions having an identical conductivity type;

a respective elevated electrode formed on the main electrodes, and having a third region including a third group IV element and a fourth group IV element and a fourth region formed on the third region and including the third group IV element;

a first silicide electrode formed in contact with the second region of the gate electrode, and being substantially free from the second group IV element; and

a second silicide electrode formed in contact with the fourth region of the elevated electrode, and being substantially free from the fourth group IV element.

Please add the following new claims 32 and 33:

32. (New) A semiconductor device comprising:

a first conductivity type insulated gate field effect transistor having a pair of first conductivity type main electrodes used as source and drain electrodes, a second conductivity type channel forming region provided between the pair of first conductivity type main electrodes, a first insulating gate film formed on the second conductivity type channel forming region, and a first gate electrode formed on the first insulating gate film, and

provided with a first region including at least a first group IV element and a second group IV element and formed in contact with the first insulating gate film, and a second region including the first group IV element and formed on the first region, the first and second regions having an identical conductivity type; and

*He*  
*do*  
*omit*  
a second conductivity type insulated gate field effect transistor having a pair of second conductivity type main electrodes used as source and drain electrodes, a first conductivity type channel forming region provided between the pair of second conductivity type main electrodes, a second insulating gate film formed on the first conductivity type channel forming region, and a second gate electrode formed on the second insulating gate film, and provided with a third region including at least the first group IV element and the second group IV element and formed in contact with the second insulating gate film, and a fourth region including the first group IV element and formed on the third region, the third and fourth regions having an identical conductivity type.

33. (New) A semiconductor device comprising:

an insulated gate field effect transistor having a pair of main electrodes used as source and drain electrodes, a channel forming region provided between the pair of main electrodes, an insulating gate film formed on the channel forming region, and a gate electrode formed on the insulating gate film, and provided with a first region including at least a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including the first group IV element and formed on the first region, the first and second regions having an identical conductivity type; and

an element isolation region formed surrounding the insulated gate field effect transistor, and having an insulating film embedded in a trench.